

-Warning-Isolated stud products should be handled with care. The ceramic used in these thyristers contains BERYLLIUM OXIDE as a major ingredient. DO NOT crush, grind, or abrade these portions if the thyristers because the dust resulting from such action may be HAZARDOUS if INHALED.

MAXIMUM RATINGS	SYMBOL	DEVICE NUMBERS		UNITS
REPETITIVE PEAK OFF-STATE VOLTAGE	200	SIPT230	SIPT240	
	400	SIPT430	SIPT440	VOLT
(1)GATE OPEN, AND TJ = 110° C /VDRM	600	SIPT630	SIPT640	
RMS ON-STATE CURRENT AT TC = 80° C AND CONDUCTION, ANGLE OF 360°	IT(RMS)	30	40	AMP
PEAK SURGE (NON-REPETITIVE) ON-STATE CURRENT, ONE-CYCLE, AT 50HZ OR 60HZ	ITSM	300	400	AMP
PEAK GATE - TRIGGER CURRENT FOR 3µSEC. MAX.	IGTM	12	12	AMP
PEAK GATE - POWER DISSIPATION AT IGT ≤ IGTM	PGM	40	40	WATT
AVERAGE GATE - POWER DISSIPATION	PG(AV)	0.75	0.75	WATT
STORAGE TEMPERATURE RANGE	TSTG	-40 to +150		°C
OPERATING TEMPERATURE RANGE, TJ	TOPER	-40 to +110		°C
PEAK OFF - STATE CURRENT (1) GATE OPEN TC = 110° C VDRM = MAX. RATING	IDRM	1.0	1.0	MA MAX.
MAXIMUM ON - STATE VOLTAGE, (1) AT TC = 25° C AND IT = RATED AMPS	VTM	2.0	2.0	VOLT MAX.
DC HOLDING CURRENT, (1) GATE OPEN AND TC = 25° C	IHO	60	60	MA MAX.
CRITICAL RATE-OF-RISE OF OFF-STATE VOLTAGE, (1) FOR VD =VDRM GATE OPEN, TC = 110° C	CRITICAL dv/dt	200	200	V/μSEC.
CRITICAL RATE-OF-RISE OF COMMUTATION VOLTAGE,(1) AT TC = 80° C, GATE UNENERGIZED, VD = VDRM, IT = IT(RMS)	COMMUTATING dv/dt	3	3	V/µSEC.
DC GATE - TRIGGER CURRENT FORVD = 12VDC. RL=30 ohm AND AT TC = 25°C (T2 + GATE + T2 - GATE-) Q1 &3 (T2 + GATE - T2 - GATE +) Q 2 & 4	IGT*	100 I, III 150 II, IV	100 I, III 150 II, IV	MA MAX.
DC GATE - TRIGGER VOLTAGE FORVD = 12VDC. RL = 30 ohm AND AT TC = 25° C	VGT	2.5	2.5	VOLT MAX.
GATE CONTROLLED TURN-ON TIME FOR VD = VDRM IGT = 200MA, TR = 0.1 μSEC.IT = 10A (PEAK) AND TC = 25° C	TGT	3	3	μSEC.
THERMAL RESISTANCE, JUNCTION-TO-CASE	R 0 J-C	2.1	2.1	°C / WATT TYP

Notes:(1) All values apply in either direction. *Other gate options available; Consult factory